

TECHNICAL DATA DATA SHEET 4170, REV. -

HERMETIC POWER SCHOTTKY RECTIFIER **Ultra Low Reverse Leakage** 200°C Operating Temperature

Applications:

· Switching Power Supply · Converters · Free-Wheeling Diodes · Polarity Protection Diode

Features:

- Ultra low Reverse Leakage Current
- Soft Reverse Recovery at Low and High Temperature
- **Very Low Forward Voltage Drop**
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics
- **Out Performs 100 Volt Ultrafast Rectifiers**
- Add Prefix C to SHD For Ceramic Seals (SHDC)
- Add Suffix S for TX/TXV screening, SS For JANS Screening

Maximum Ratings:

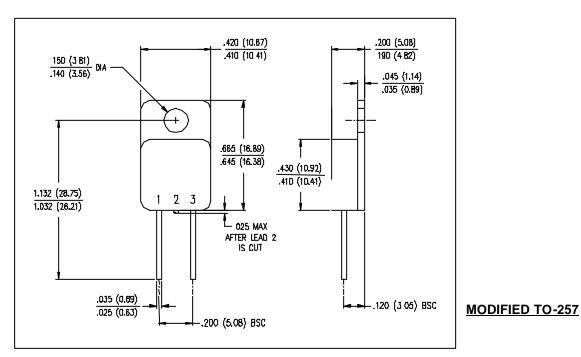
Characteristics	Symbol	Condition	Max.	Units	
Peak Inverse Voltage	V_{RWM}	-	100	V	
Max. Average Forward Current	I _{F(AV)}	50% duty cycle, rectangular wave form	15	Α	
Max. Peak One Cycle Non- Repetitive Surge Current	I _{FSM}	8.3 ms, half Sine wave	150	Α	
Max. Thermal Resistance	$R_{ heta JC}$		2.1	°C/W	
Max. Junction Temperature	TJ	-	-65 to +200	°C	
Max. Storage Temperature	T _{sta}	-	-65 to +175	°C	

Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	V_{F1}	@ 15A, Pulse, T _J = 25 °C	0.93	V
	V_{F2}	@ 15A, Pulse, T _J = 125 °C	0.84	V
Max. Reverse Current	I _{R1}	@V _R = 100V, Pulse,	.01	mA
		$T_J = 25 ^{\circ}C$		
	I_{R2}	@V _R = 100V, Pulse,	1.0	mA
		T _J = 125 °C		
Max. Junction Capacitance	C_T	$@V_R = 5V, T_C = 25 ^{\circ}C$	500	pF
		$f_{SIG} = 1MHz,$		
		$V_{SIG} = 50 \text{mV (p-p)}$		

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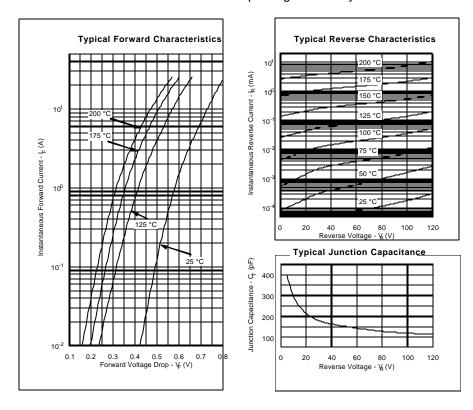
Mechanical Dimensions: In Inches / mm



PINOUT TABLE

TYPE	PIN 1	PIN 2	PIN 3
SINGLE RECTIFIER	CATHODE	-	ANODE

Note: The V_f curves shown are for the SD125SCU100 unpackaged die only.





TECHNICAL DATA

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